

N-channel TrenchMOS logic level FET Rev. 02 — 7 February 2011

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- **1.3 Applications**
 - 12 V and 24 V loads
 - Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	43	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	94	W

Suitable for logic level gate drive sources

- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids



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Table 1.	Quick reference da	tacontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
R _{DSon} drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \; V; \; I_{D} = 25 \; A; \\ T_{j} = 25 \; ^{\circ}C \end{array}$	-	-	27	mΩ	
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$	-	19	22	mΩ	
	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{\text{See } \frac{\text{Figure } 13}{\text{See } \frac{12}{3}}$	-	21	25	mΩ	
Avalanche	e ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 43 \text{ A}; \text{V}_{\text{sup}} \leq 55 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 5 \text{ V}; \\ T_{j(\text{init})} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-	-	123	mJ

Table 1.	Quick	reference	data	continued
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Pinning information 2.

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbbo76 S

SOT428 (DPAK)

Ordering information 3.

Table 3. Orderin	information		
Type number	Package		
	Name	Description	Version
BUK9225-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

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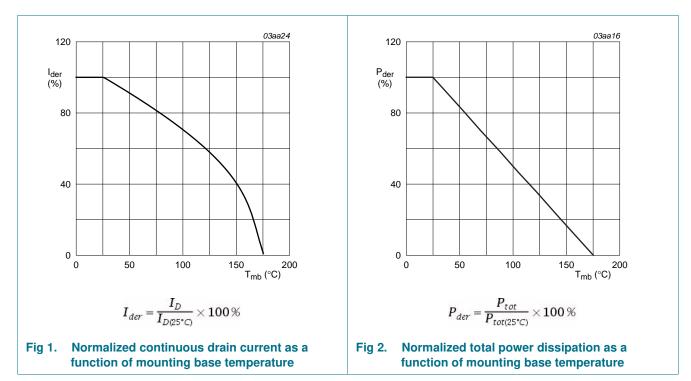
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

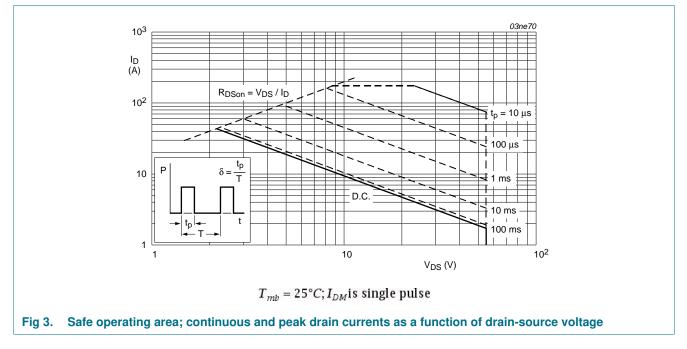
Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V _{GS}	gate-source voltage		-15	15	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	-	43	A
		T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>	-	30	А
I _{DM}	peak drain current	$T_{mb} = 25 \text{ °C}; \text{ pulsed}; t_p \le 10 \mu\text{s};$ see Figure 3	-	173	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	94	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	43	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	173	Α
Avalanche r	ruggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ I_D = 43 \text{ A}; V_{sup} \leq 55 \text{ V}; \text{R}_{GS} = 50 \Omega; \\ V_{GS} = 5 \text{ V}; \text$	-	123	mJ

[1] peak drain current is limited by chip, not package.



BUK9225-55A

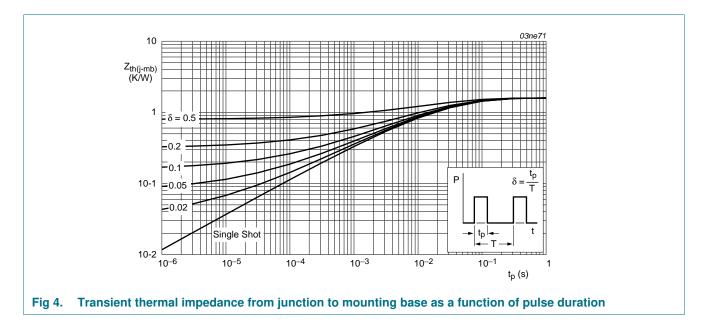
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	71.4	-	K/W

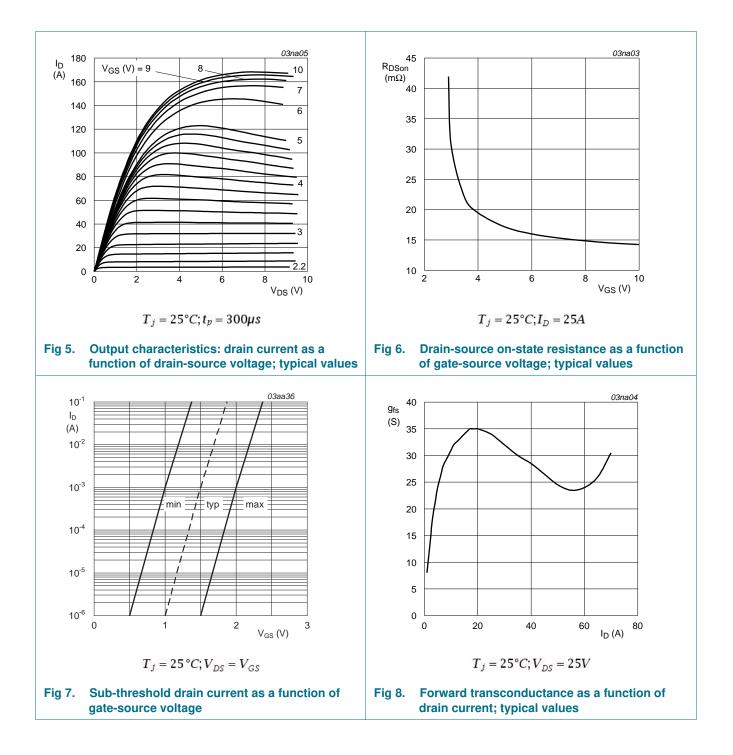


6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 11</u>	1	1.5	2	V
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 11</u>	-	-	2.3	V	
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u>	0.5	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V_{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	27	mΩ
	resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	50	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	19	22	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	21	25	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1360	1724	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	240	287	pF
C _{rss}	reverse transfer capacitance		-	160	222	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	17	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	104	-	ns
t _{d(off)}	turn-off delay time		-	82	-	ns
t _f	fall time		-	80	-	ns
L _D	internal drain inductance	measured from drain to centre of die ; $T_j = 25 \ ^\circ C$	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	Irain diode					
V_{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; see Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs; V _{GS} = -10 V; V _{DS} = 30 V; T _j = 25 °C	-	50	-	ns

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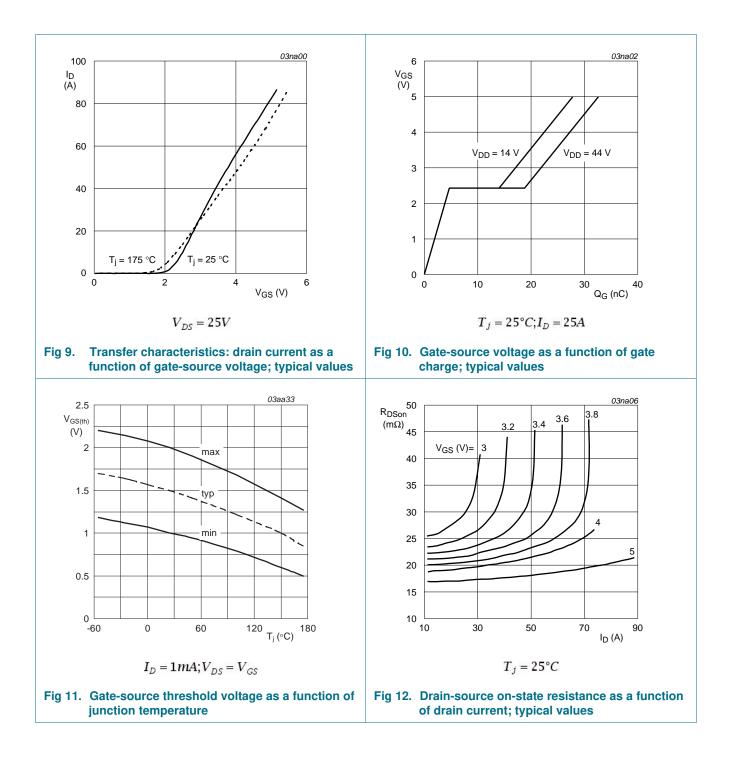
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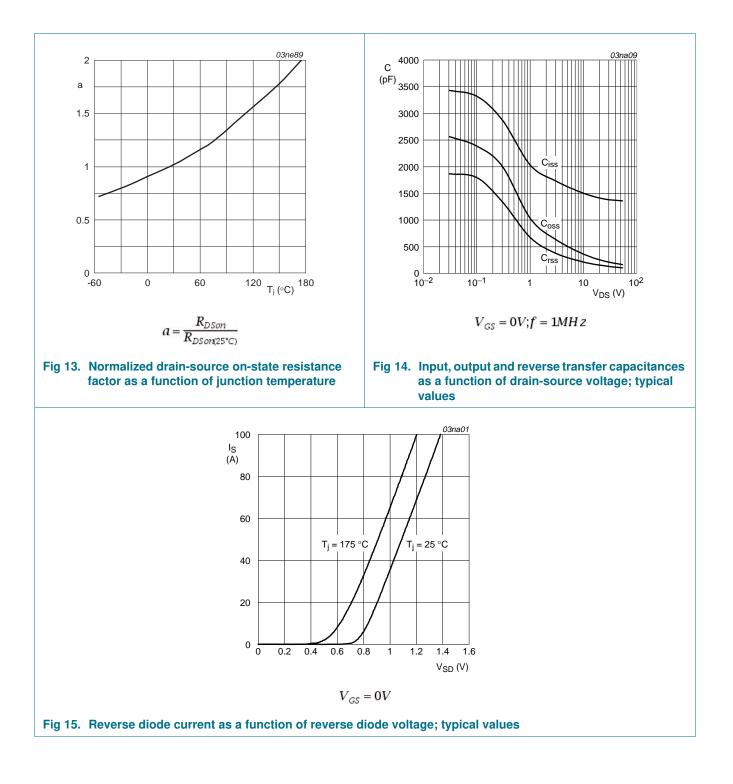
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7. Package outline

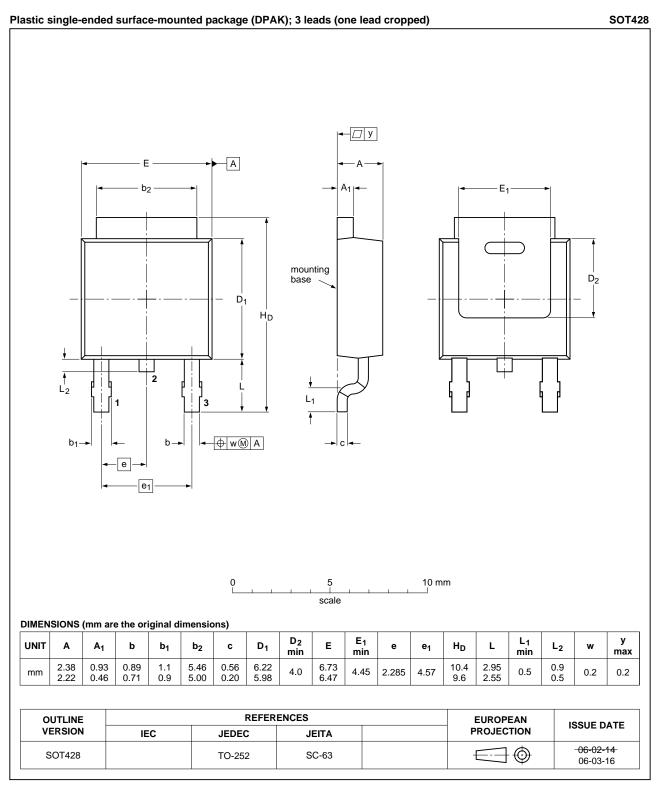


Fig 16. Package outline SOT428 (DPAK)

BUK9225-55A Product data sheet

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8. Revision history

Table 7. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9225-55A v.2	20110207	Product data sheet	-	BUK9225-55A v.1
Modifications:	of NXP Semic • Legal texts ha	this data sheet has been rea conductors. we been adapted to the new ges to content.	· · ·	
BUK9225-55A v.1	20010417	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia.com</u>.

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